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SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

MMSD4148T1G-MS


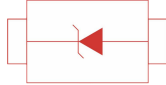

Product specification

Silicon Epitaxial Planar Switching Diode

Features

- SOD-123 package
- Fast switching

Reference News

SOD-123	CIRCUIT DIAGRAM	MARKING
		

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

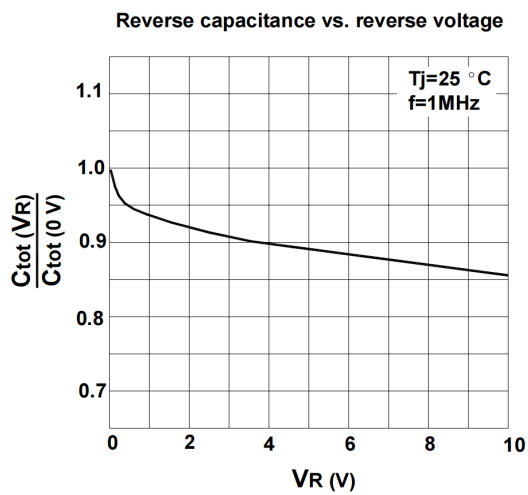
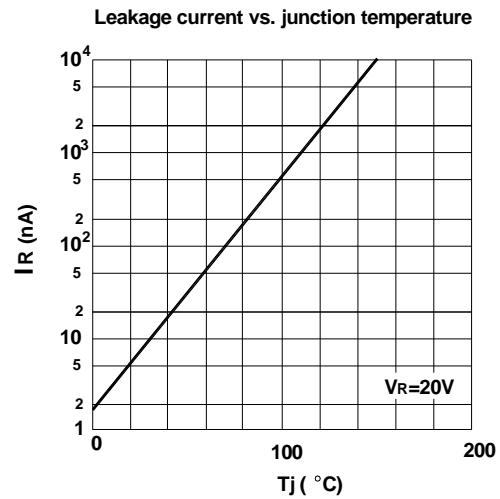
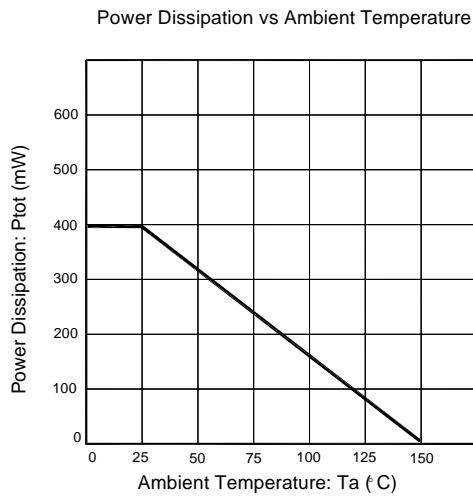
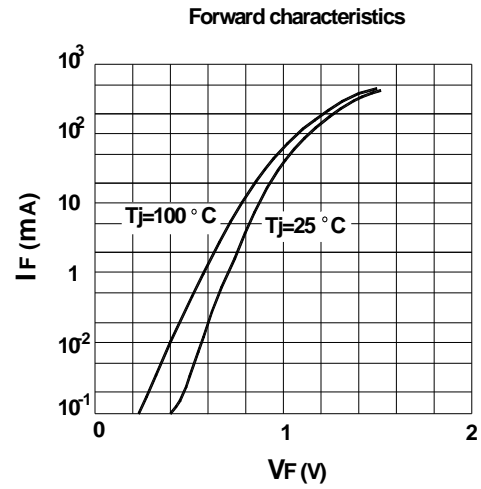
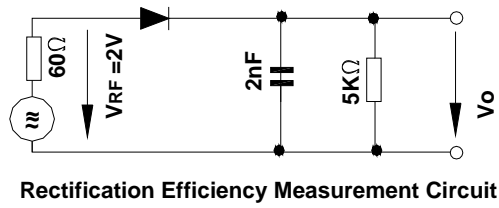
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	0.5 1 4	A
Power Dissipation	P_{tot}	400	mW
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	312	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

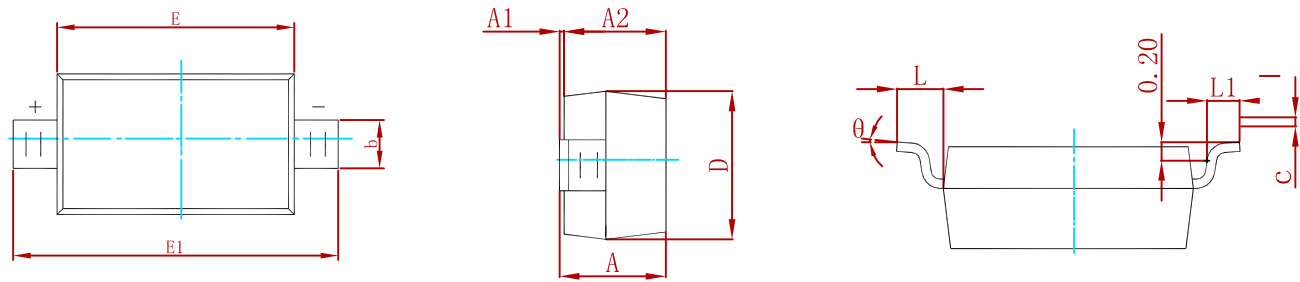
Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	V_F	- - - -	0.715 0.855 1 1.25	V
Peak Reverse Current at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$, $T_J = 150^\circ\text{C}$ at $V_R = 25\text{ V}$, $T_J = 150^\circ\text{C}$	I_R	- - - -	1 25 50 30	μA nA μA μA
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	-	2	pF
Reverse Recovery Time at $I_{rr} = 0.1 \times I_R$, $I_F = I_R = 10\text{ mA}$, $R_L = 100\ \Omega$	t_{rr}	-	4	ns

Typical Characteristics

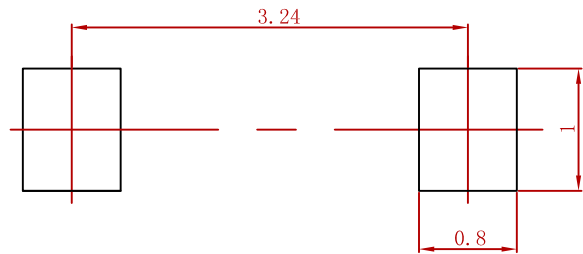


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.450	0.650	0.018	0.026
c	0.080	0.150	0.003	0.006
D	1.500	1.700	0.059	0.067
E	2.600	2.800	0.102	0.110
E1	3.550	3.850	0.140	0.152
L	0.500 REF		0.020 REF	
L1	0.250	0.450	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
1.Controlling dlmenslon:in mllimeters.
2.General tolerance:± 0.05mm.
3.The pad layout ls for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMSD4148T1G-MS	SOD-123	3000

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